

FIG. 1

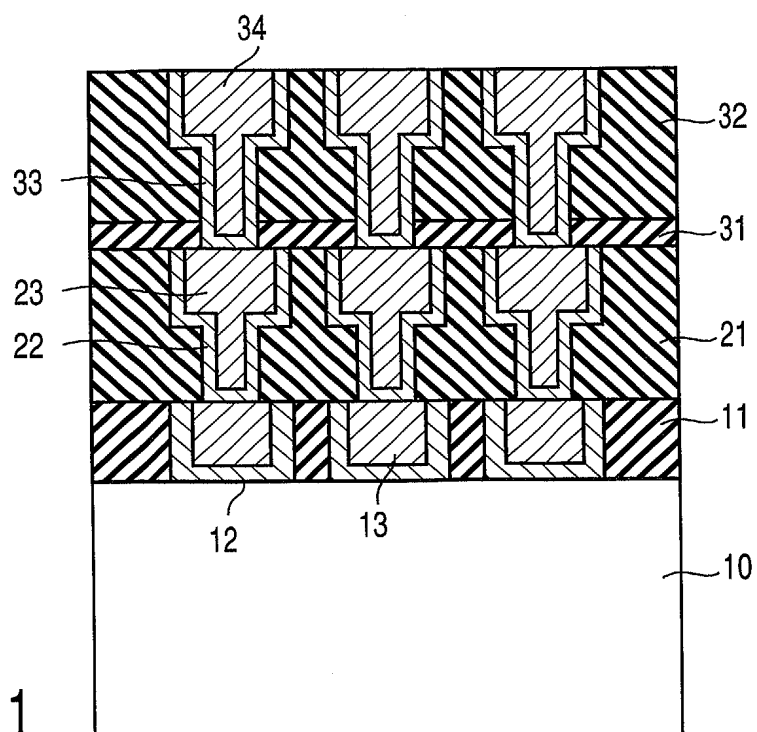


FIG. 2A

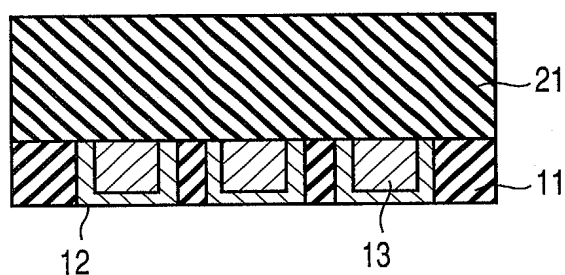


FIG. 2B

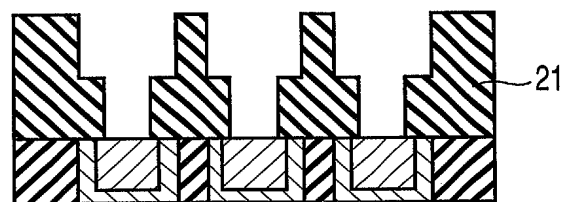


FIG. 2C

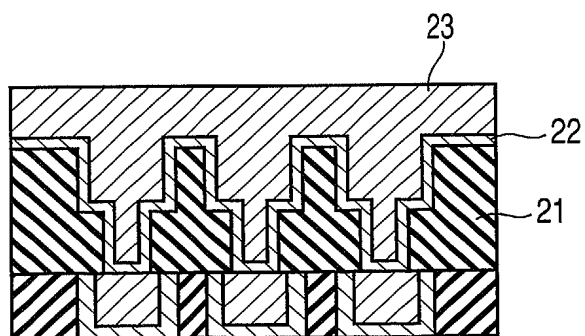
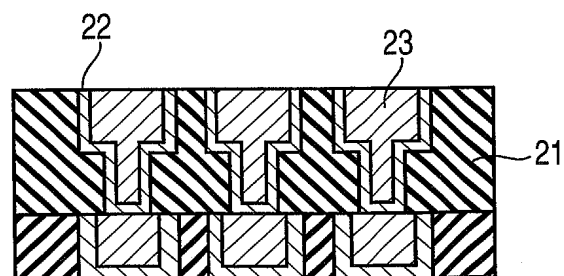


FIG. 2D



A cross-sectional view of a semiconductor device. It features a substrate 32 with a grid of protrusions 33. A top layer 34 is deposited over the protrusions. The protrusions are arranged in a regular grid pattern.

FIG. 3A

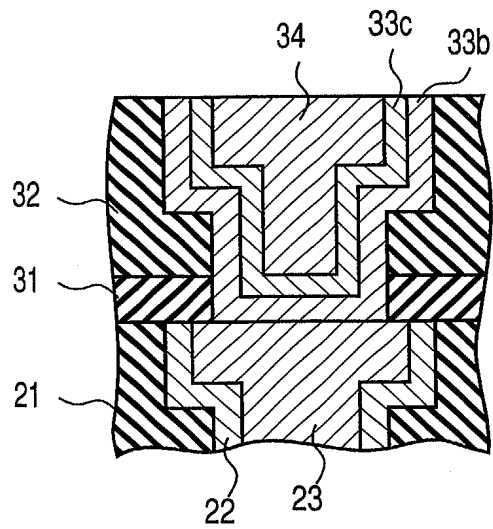


FIG. 3B

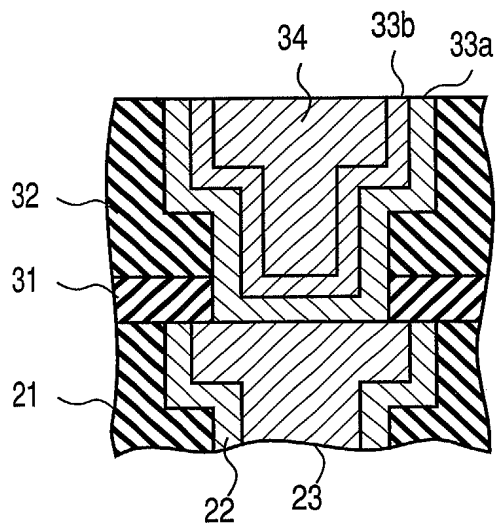
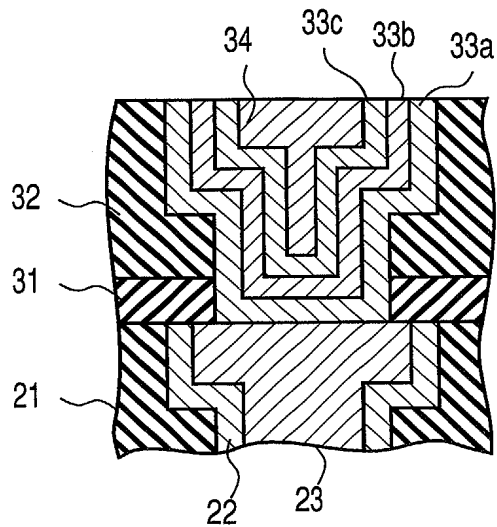


FIG. 3C



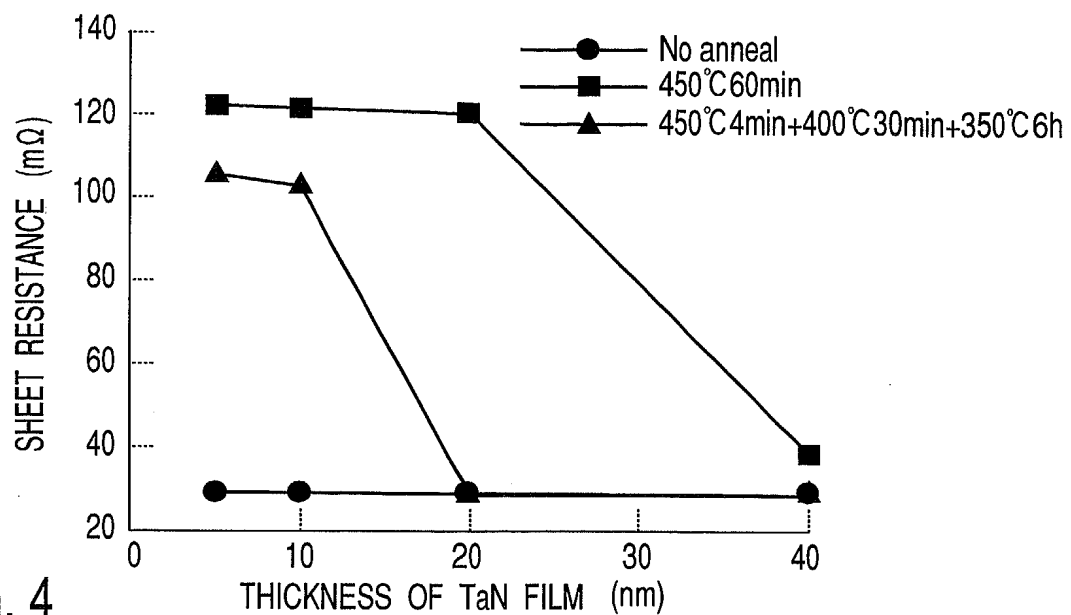


FIG. 4

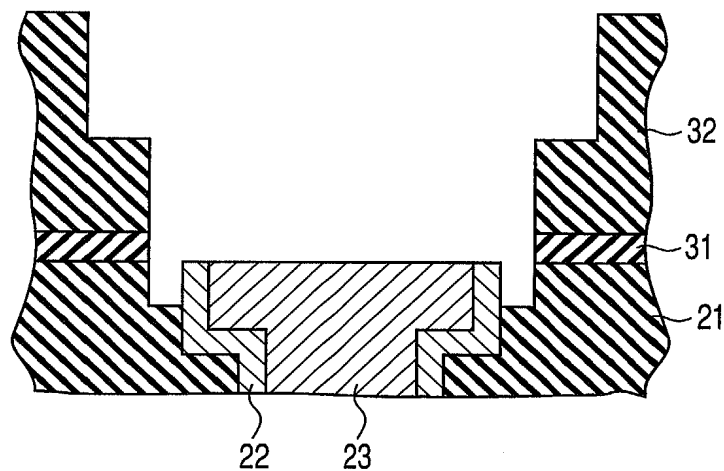


FIG. 5

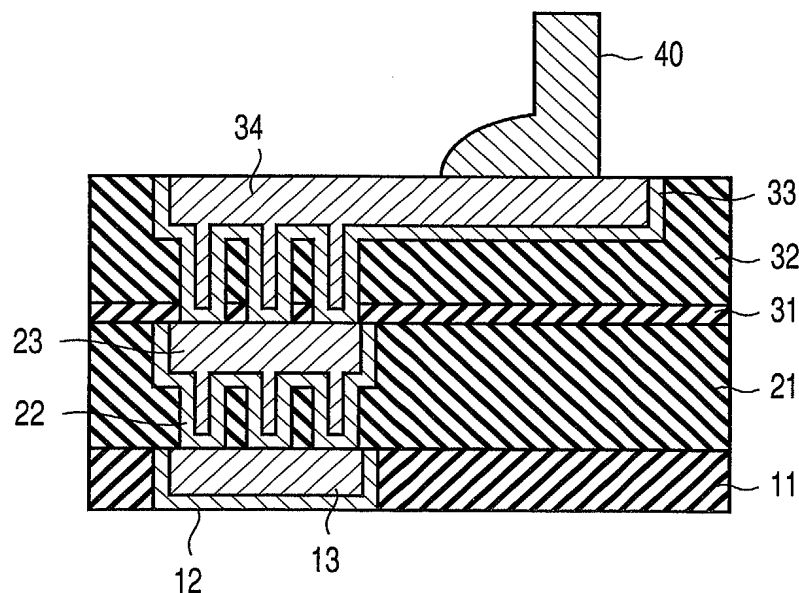


FIG. 6

FIG. 7A

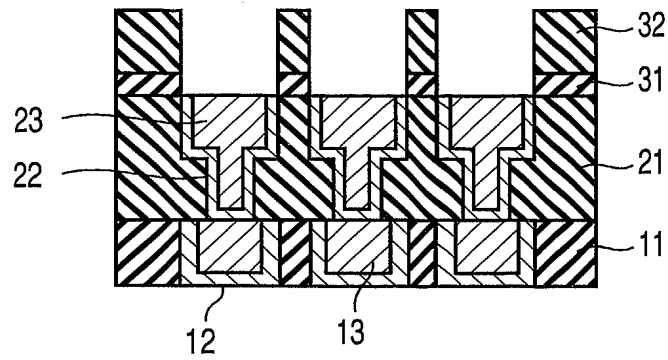


FIG. 7B

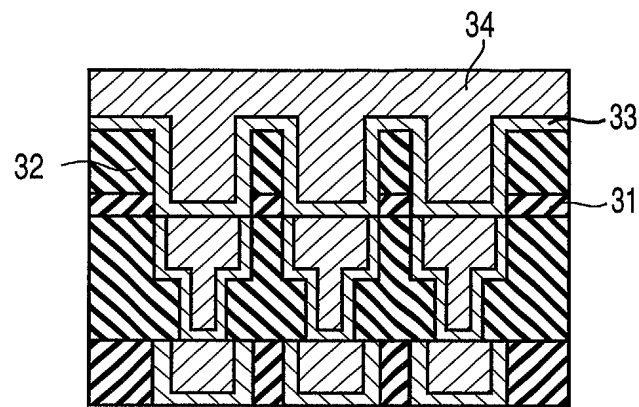


FIG. 7C

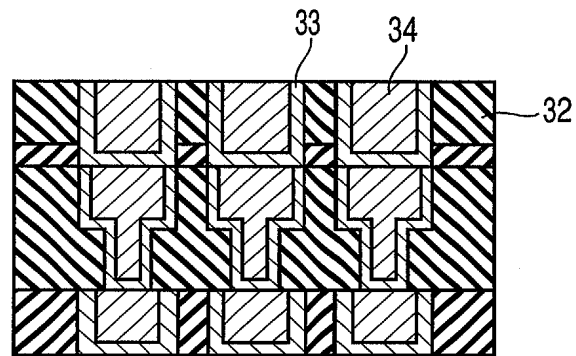


FIG. 7D

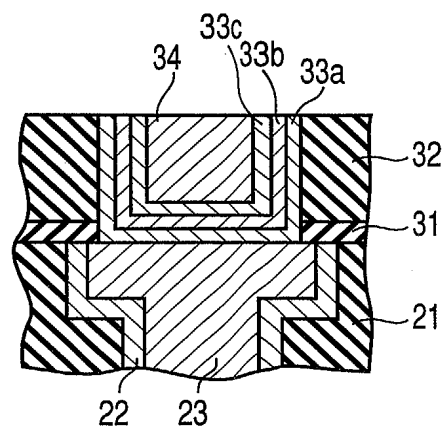


FIG. 8A

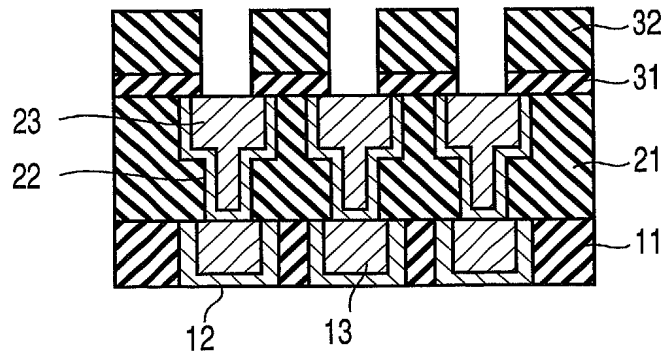


FIG. 8A

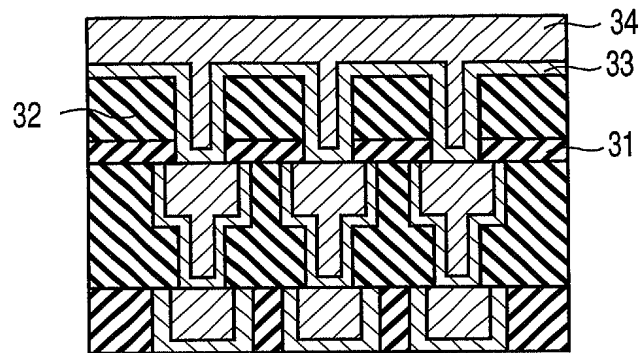


FIG. 8B

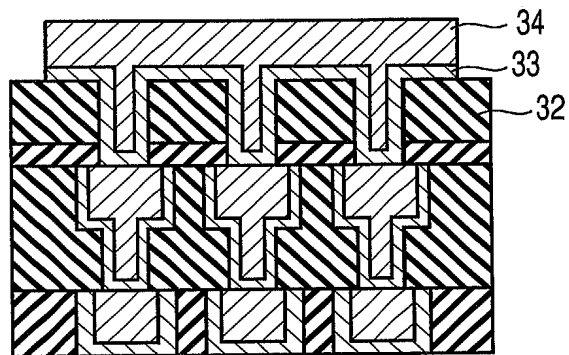


FIG. 8C

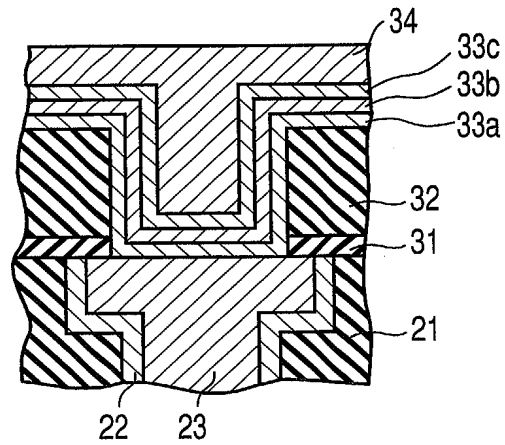


FIG. 8D

FIG. 9A

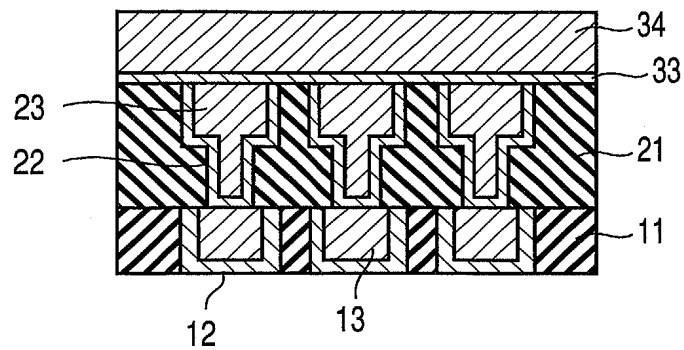


FIG. 9B

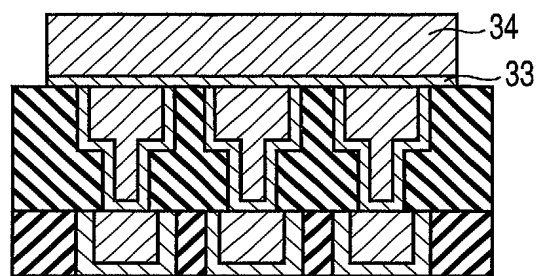


FIG. 9C

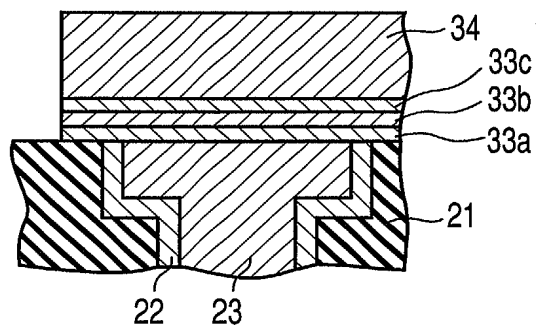


FIG. 10
(PRIOR ART)

